



General Description

The IAUC45N04S6N070HATMA1 use advanced SGT MOSFET technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness.

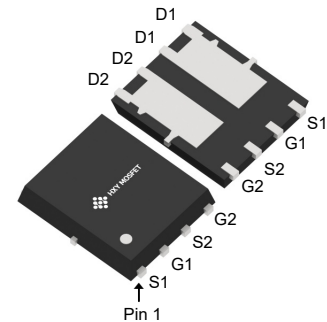
General Features

$V_{DS} = 40V$ $I_D = 40A$

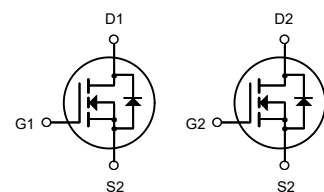
$R_{DS(ON)} < 8.5m\Omega @ V_{GS} = 10V$

Applications

Consumer electronic power supply Motor control
Synchronous-rectification Isolated DC
Synchronous-rectification applications



DFN5X6B-8L



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IAUC45N04S6N070HATMA1	DFN5X6B-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	40	A
		$T_C = 100^\circ C$	25	A
I_{DM}	Pulsed Drain Current ^{note1}		100	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		28	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	29	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.2	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	$^\circ C$



Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=12A$	---	6.9	8.5	$m\Omega$
		$V_{GS}=4.5V$, $I_D=10A$	---	10.0	15	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.35	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=32V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=32V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V$, $V_{GS}=4.5V$, $I_D=12A$	---	5.8	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	1.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	14.3	---	ns
T_r	Rise Time		---	5.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	20	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	690	---	pF
C_{oss}	Output Capacitance		---	193	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	40	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=31A$
- 4.The power dissipation is limited by 150 $^{\circ}\text{C}$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

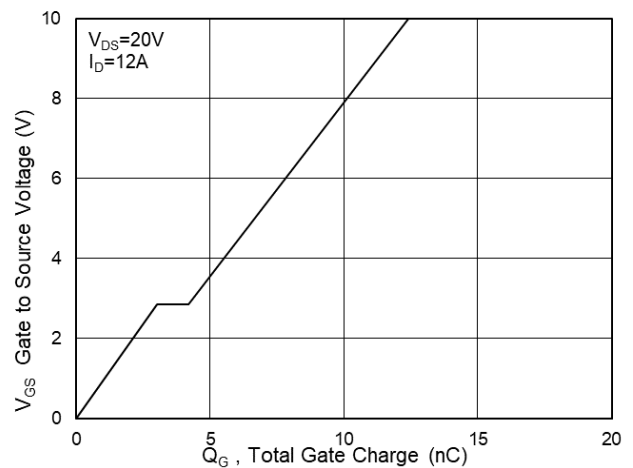
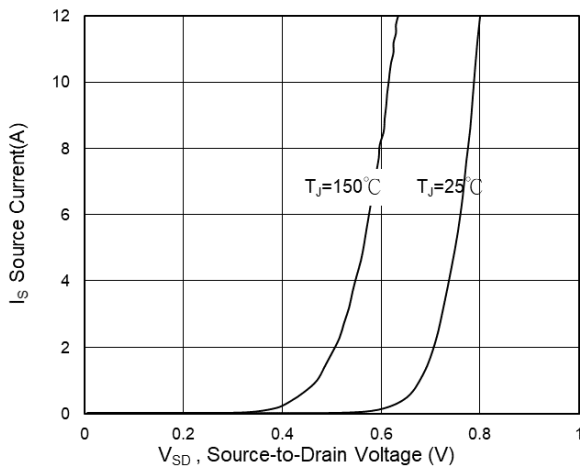
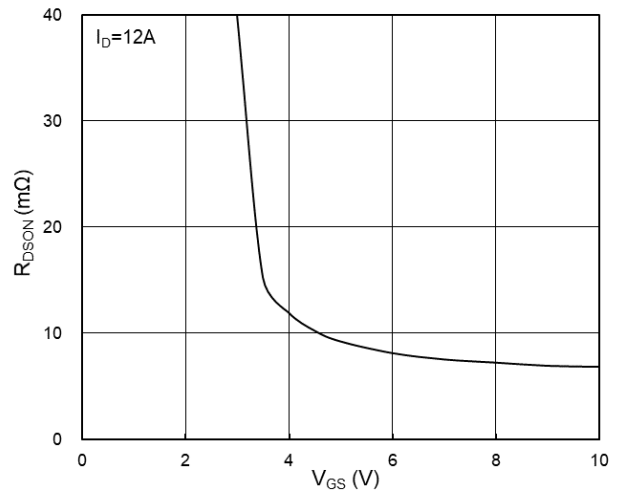
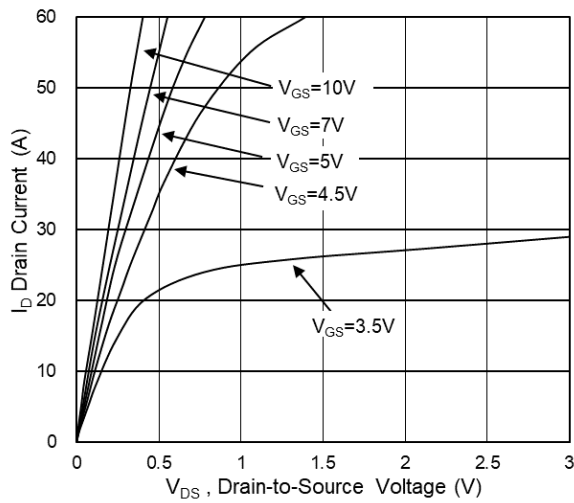
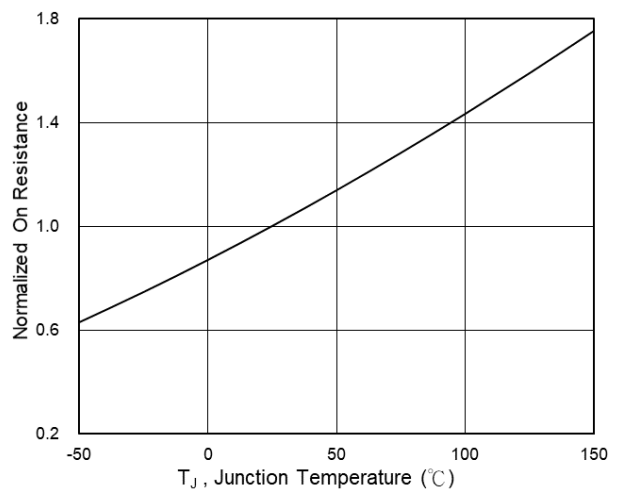
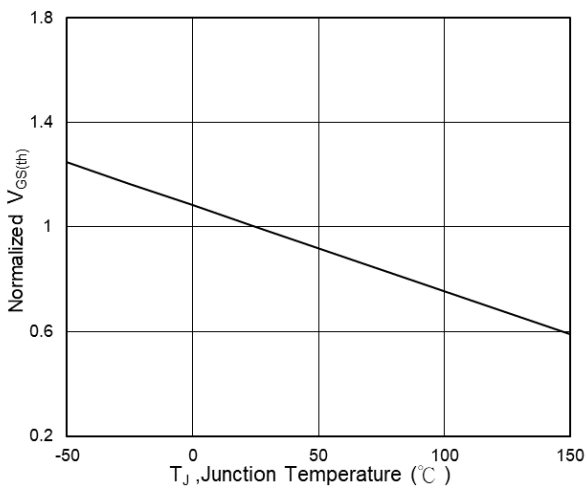


Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics



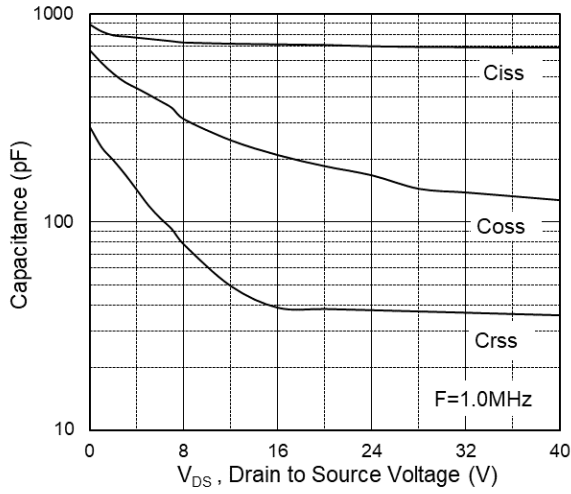


Fig.7 Capacitance

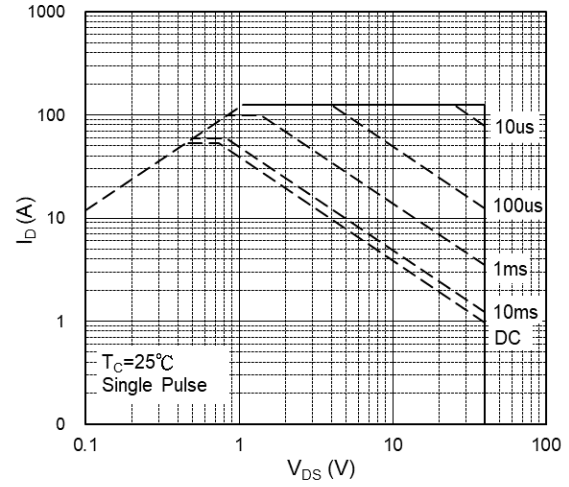


Fig.8 Safe Operating Area

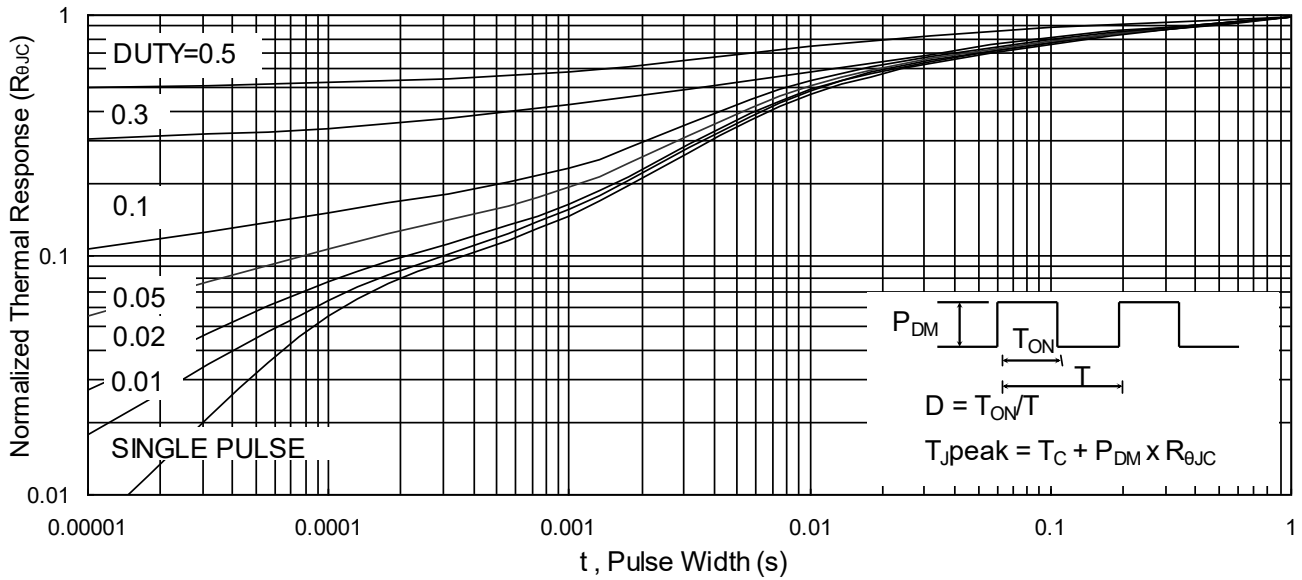


Fig.9 Normalized Maximum Transient Thermal Impedance

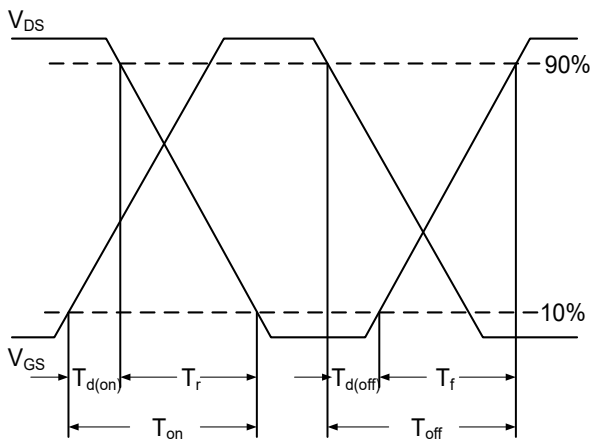


Fig.10 Switching Time Waveform

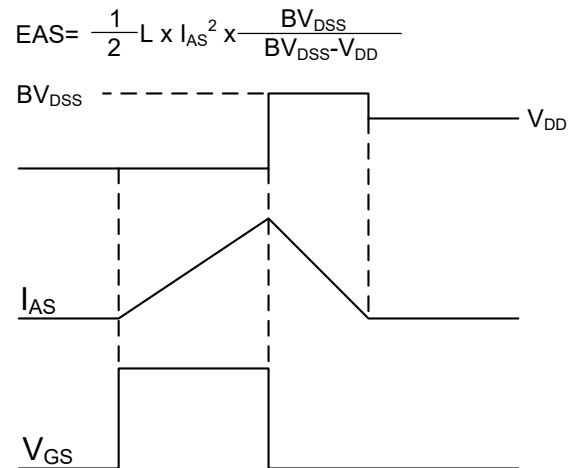
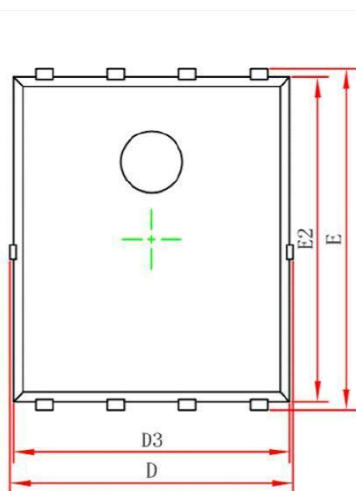


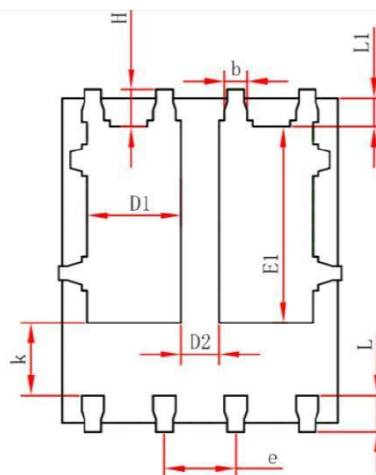
Fig.11 Unclamped Inductive Waveform



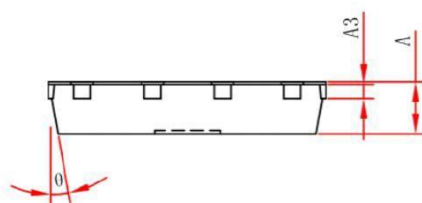
Package Mechanical Data-DFN5X6B-8L



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.154REF.		0.006REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



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